

Docket No.: 63979-028

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277

Takashi NISHIKAWA, et al. : Confirmation Number: 2411

Serial No.: 10/616,917 : Group Art Unit: 2811

Filed: July 11, 2003 : Examiner: Unknown

For: A SEMICONDUCTOR DEVICE AND A FABRICATION METHOD THEREOF

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Upon review of the PTO-Form 1449 filed on October 9, 2003, the client has noted an inverted error in one of the references. Its is respectfully requested that the revised Form 1449 herein be considered. The references listed have already been submitted to the PTO.

This Supplemental Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

10/616,917

Each non-English language reference was cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the foreign search report or office action, together with an English language version thereof, is attached for the

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Respectfully submitted,

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Examiner's information.

Date: December 9, 2003

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached

